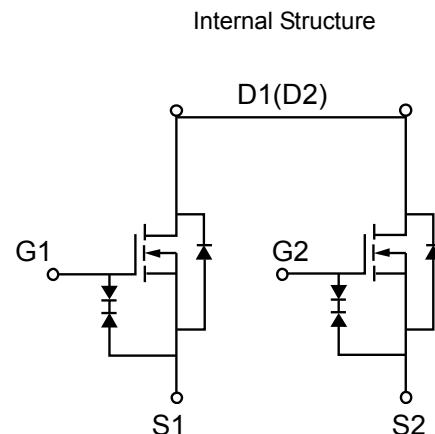
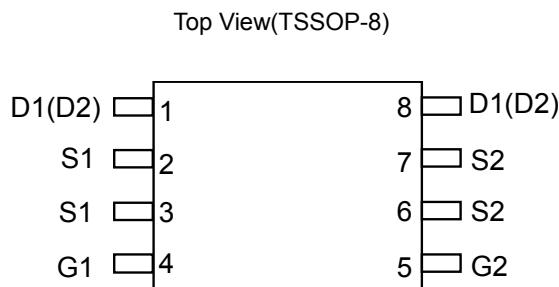


## Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
20	19@ VGS=4.5V	6



## Absolute maximum rating@25°C

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current (T <sub>J</sub> =150°C)	I <sub>D</sub>	6	A
T <sub>A</sub> =70°C	5.5		
Pulsed Drain Current	I <sub>DM</sub>	25	A
Maximum Power Dissipation	P <sub>D</sub>	1.5	W
T <sub>A</sub> =70°C	0.96		
Operating Junction and Storage Temperature Range	T <sub>J</sub>	-55 to 150	°C

## Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient	t≤10s	R <sub>θJA</sub>	64	°C/W
Maximum Junction-to-Ambient	Steady-State		89	°C/W
Maximum Junction-to-Lead	Steady-State	R <sub>θJL</sub>	53	°C/W

## Dual N-Channel MOSFET

PDNM8TP20V6E

Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	20		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	$\pm 10$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.6	0.8	1.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 6.0A$	-	19	24	$m\Omega$
		$V_{GS} = 2.5V, I_D = 5.5A$	-	25	30	
		$V_{GS} = 1.8V, I_D = 2A$		35	50	
Total Gate Charge	$Q_g$	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$		18	22	$nC$
Total Gate Charge	$Q_g$	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6A$		10	12	
Gate-Source Charge	$Q_{gs}$			2.2		
Gate-Drain Charge	$Q_{gd}$			3.6		
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$	-	245	300	pF
Output Capacitance	$C_{oss}$		-	90		pF
Reverse Transfer Capacitance	$C_{rss}$		-	26		pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10V, V_{GEN} = 4.5V, R_G = 6\Omega, R_L = 10\Omega, I_D = 1A$	-	140	200	ns
Turn-Off Delay Time	$t_{d(off)}$		-	390	450	ns
Turn-On Rise Time	$t_r$		-	210	250	ns
Turn-On Fall Time	$t_f$		-	220	260	ns
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 1.5A$		0.73	1.2	V

## Typical Characteristics

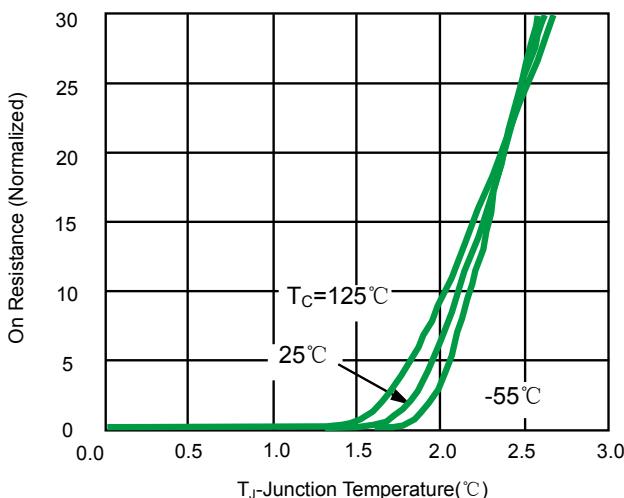


Fig 1. On Resistance vs. Junction Temperature

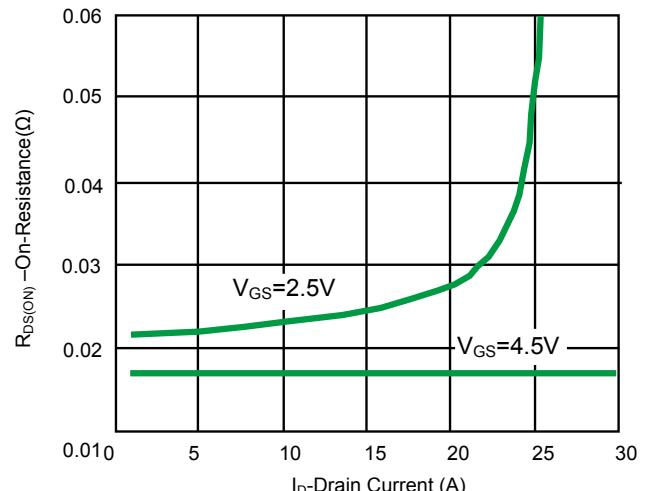


Fig 2. On-Resistance vs. Drain Current

## Dual N-Channel MOSFET

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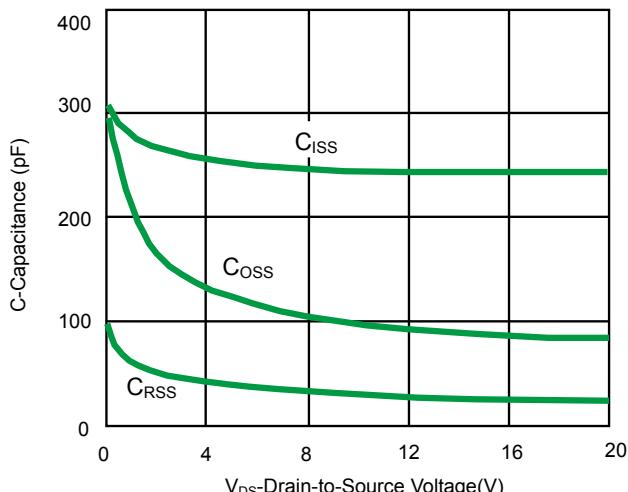


Fig 3. Capacitance

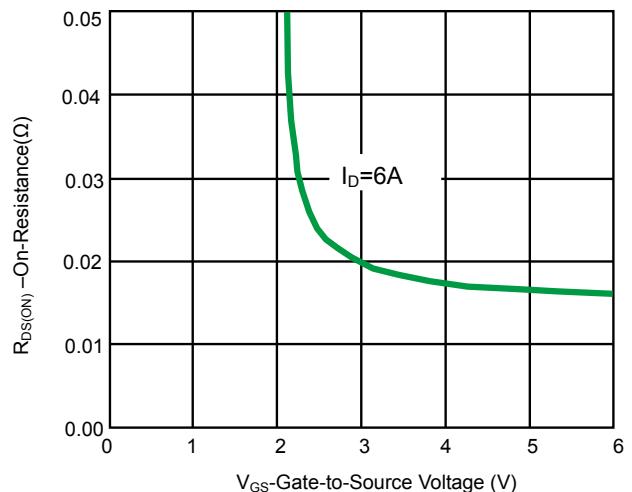


Fig 4. On-Resistance vs. Gate-to-Source Voltage

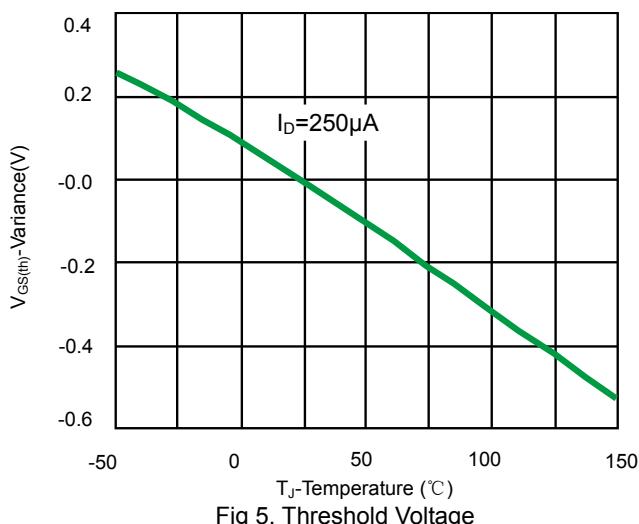


Fig 5. Threshold Voltage

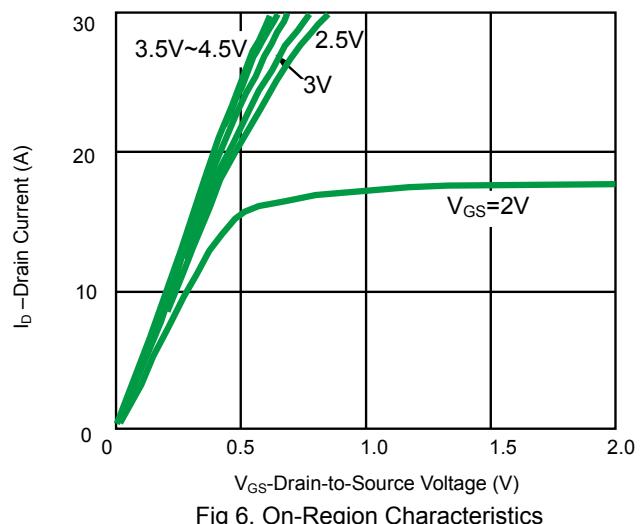


Fig 6. On-Region Characteristics

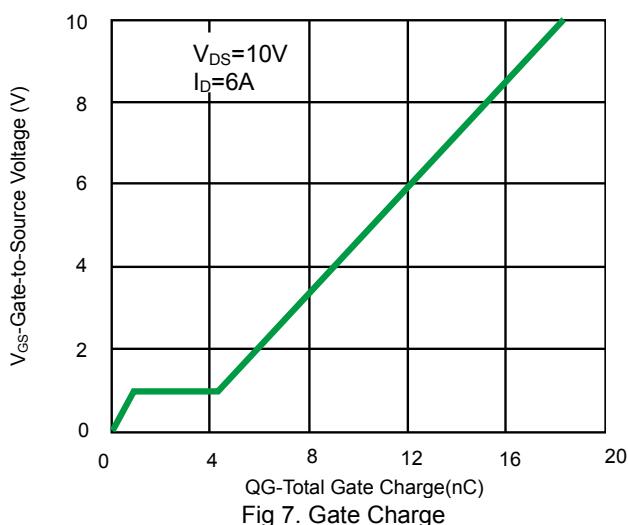


Fig 7. Gate Charge

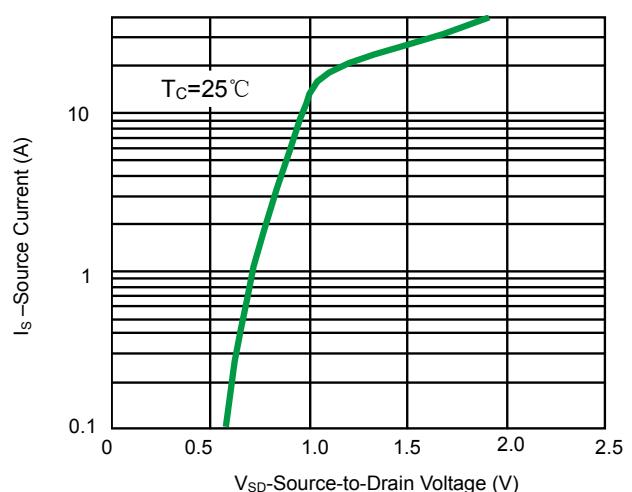


Fig 8. On-Resistance vs. Drain Current

## Dual N-Channel MOSFET

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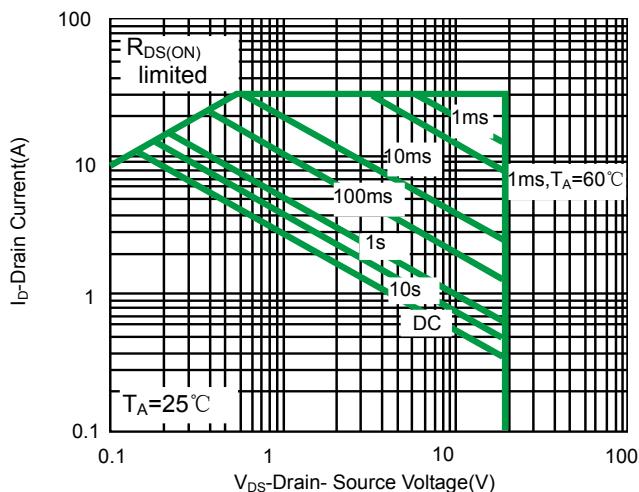


Fig 9. Maximum Forward Biased Safe Operating Area

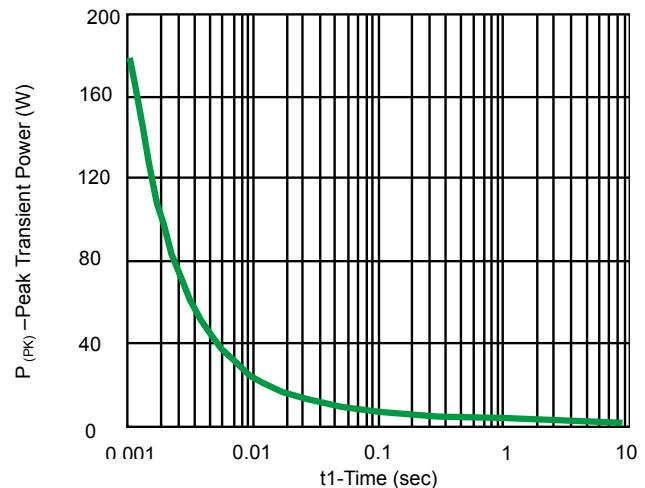


Fig 10. Single Pulse Maximum Power Dissipation

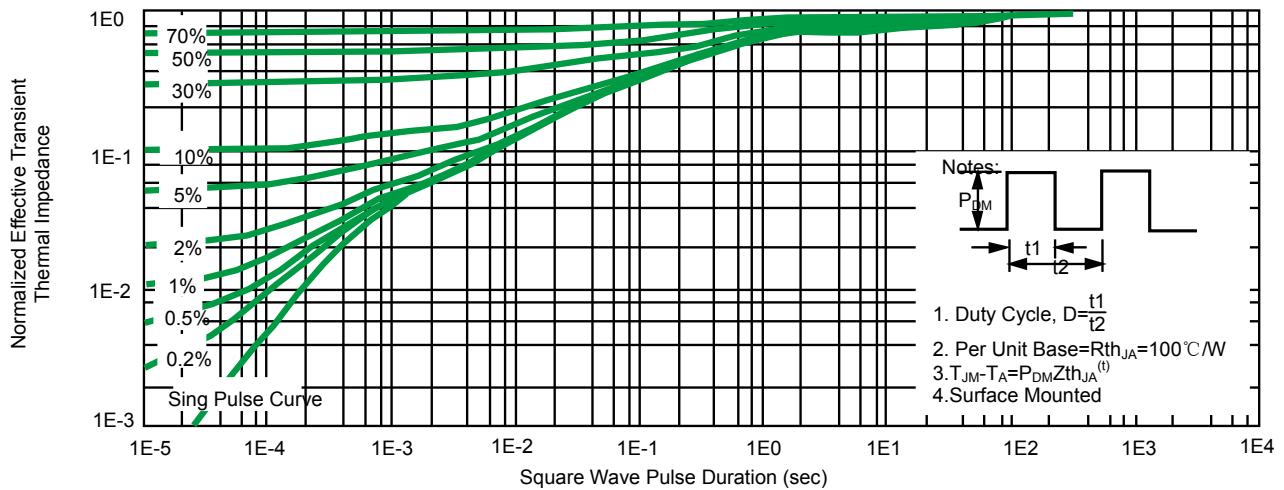
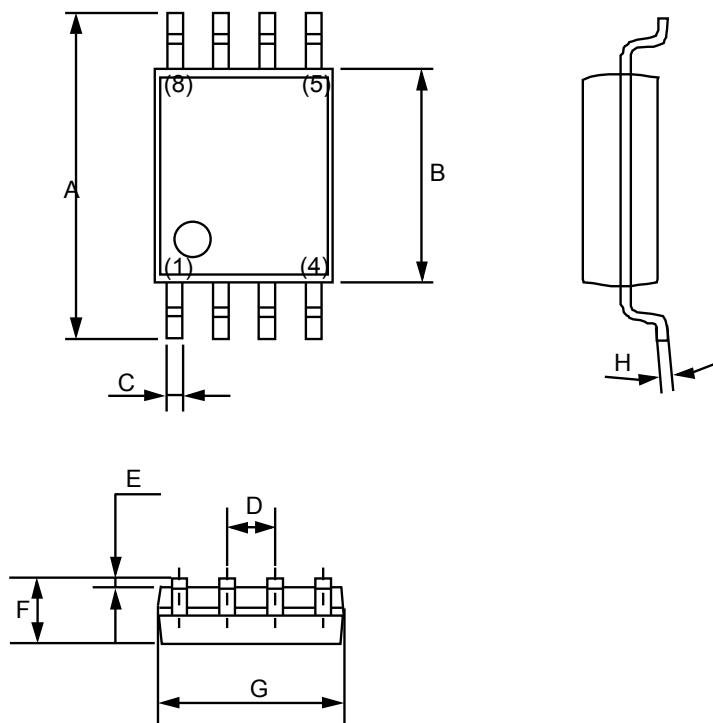


Fig 11. Normalized Thermal Transient Impedance, Junction-to-Ambient

## Product dimension(TSSOP-8)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	6.250	6.550	0.246	0.258
B	4.300	4.500	0.169	0.177
C	0.190	0.300	0.007	0.012
D	0.65(BSC)		0.026(BSC)	
E	0.020	0.150	0.001	0.006
F	0.800	1.000	0.031	0.039
G	2.900	3.100	0.114	0.122
H	0.090	0.200	0.004	0.008

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